# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







DMN2600UFB

#### 25V N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- **ESD Protected Gate 1kV**
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: X1-DFN1006-3 •
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @4)
- Weight: 0.001 grams (Approximate)

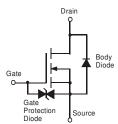




X1-DFN1006-3

Bottom View





Top View Internal Schematic

Equivalent Circuit

### Ordering Information (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
DMN2600UFB-7	NA	7	8	3000	
DMN2600UFB-7B NA 7		7	8	10,000	
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.					

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**

DMN2600UFB-7	From date code 1527 (YYWW), this changes to: Top View Dot Denotes Drain Side Top View Bar Denotes Gate and Source Side Top View Bar Denotes Gate and Source Side
DMN2600UFB-7B	Top View Bar Denotes Gate and Source Side NA = Part Marking Code



#### Maximum Ratings (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	25	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 4)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C	ID	1.3 0.9	А
Pulsed Drain Current			I <sub>DM</sub>	3.0	A

#### Thermal Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	PD	0.54	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$	R <sub>0JA</sub>	234	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

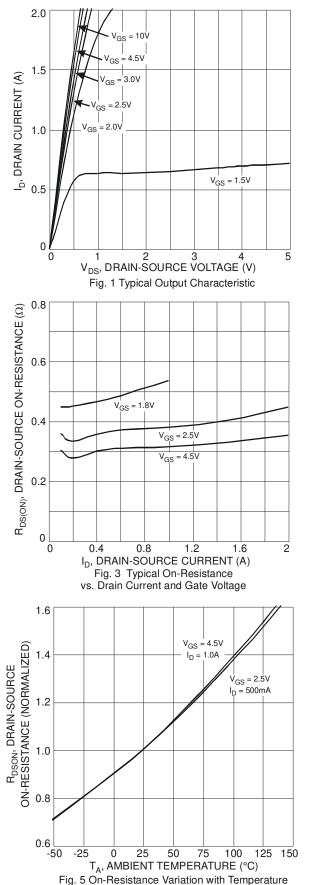
Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)	oyinbol		• 76	ших	0		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	25	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	1	μA	$V_{DS} = 25V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	-	-	10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.45	-	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
				350		$V_{GS} = 4.5V, I_D = 200mA$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	-	450	mΩ	$V_{GS} = 2.5V, I_D = 100mA$	
				600		$V_{GS} = 1.8V, I_D = 75mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	40	-	-	mS	$V_{DS} = 3V, I_D = 200mA$	
Diode Forward Voltage	V <sub>SD</sub>	-	-	1.2	V	$V_{GS} = 0V, I_{S} = 300mA$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	Ciss	-	70.13	-	pF		
Output Capacitance	Coss	-	7.56	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	5.59	-	pF		
Gate Resistance	Rg	-	72.3	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	-	0.85	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	0.16	-	nC	$-V_{GS} = 4.5V, V_{DS} = 15V,$ $-I_{D} = 1A$	
Gate-Drain Charge	Q <sub>gd</sub>	-	0.11	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	4.1	-	ns		
Turn-On Rise Time	tr	-	11.5	-	ns	V <sub>DS</sub> = 15V, R <sub>L</sub> =15Ω	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	34.8	-	ns	$V_{GS} = 10V, R_G = 6\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	-	20.9	-	ns		

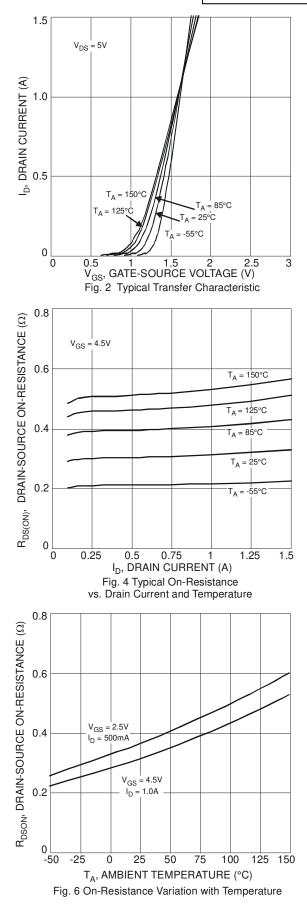
Notes: 4. Device mounted on FR-4 substrate PCB board, with minimum recommended pad layout.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.



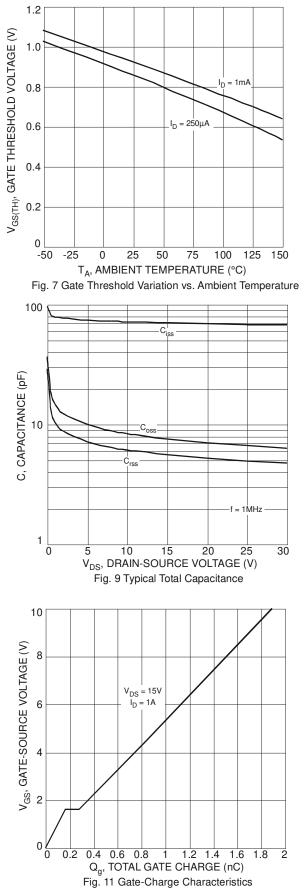


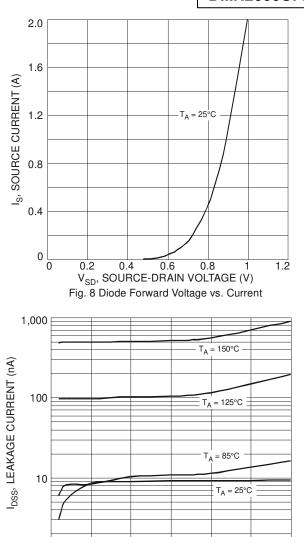






### DMN2600UFB





10 15 20 25 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

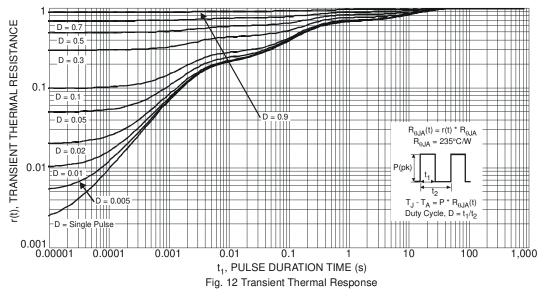
1

ō

5

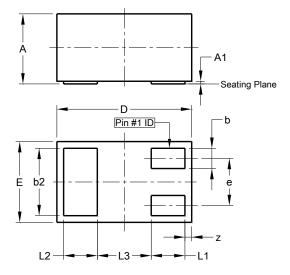
30





# **Package Outline Dimensions**

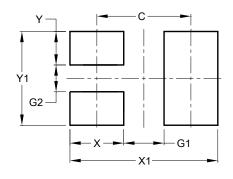
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	-	-	0.35		
L1	0.20	0.30	0.25		
L2 0.20 0.30 0.25					
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

## Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Dimensions	Value (in mm)			
С	0.70			
G1	0.30			
G2	0.20			
Х	0.40			
X1	1.10			
Ŷ	0.25			
Y1	0.70			



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

- 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for
  - use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2015, Diodes Incorporated

www.diodes.com